

First Named Inventor	Leonard Forbes	<p align="center">SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT FORM PTO-1449</p>
Serial No.	10/808,058	
Filing Date	March 24, 2000	
Group Art Unit	2818	
Examiner Name	Unknown	
Confirmation No.	4217	
Attorney Docket No.	400.288USO	
Title: MEMORY DEVICE WITH HIGH DIELECTRIC CONSTANT GATE DIELECTRICS AND METAL FLOATING GATES		Sheet 1 of 1

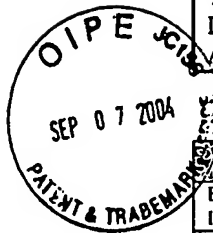
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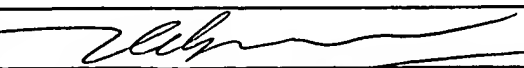


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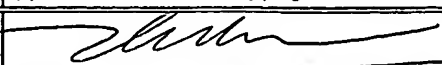
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